MOSFETs Silicon Carbide N-Channel MOS

# TW015N65C

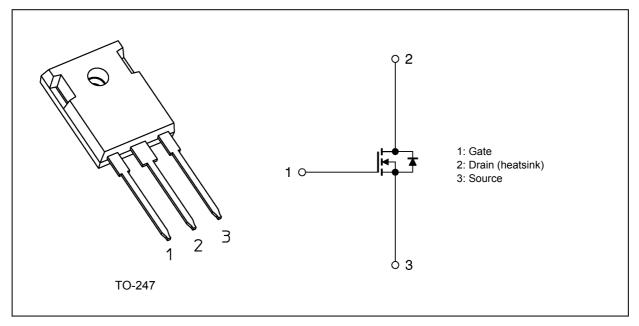
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage:  $V_{DSF}$  = -1.35 V (typ.)
- (3) High voltage:  $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 15 \text{ m}\Omega$  (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage:  $V_{th}$  = 3.0 to 5.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 11.7 mA)
- (6) Enhancement mode.

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25 \ ^{\circ}C$ unless otherwise specified)

	Characteristics	Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	650	V
Gate-source voltage		V <sub>GSS</sub>	+25/-10	
Drain current (DC)	( T <sub>c</sub> = 25 °C )	I <sub>D</sub>	100	A
Drain current (DC)	( T <sub>c</sub> = 100°C )	I <sub>D</sub>	82	
Drain current (pulsed)	( T <sub>c</sub> = 25 °C )	I <sub>DP</sub>	360	
Drain current (pulsed)	( T <sub>c</sub> = 100°C )	I <sub>DP</sub>	270	
Power dissipation	( T <sub>c</sub> = 25°C )	PD	342	W
Channel temperature		T <sub>ch</sub>	175	°C
Storage temperature		T <sub>stg</sub>	-55 to 175	
Mounting torque		TOR	0.8	N·m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	0.438	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	50	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.

### 6. Electrical Characteristics

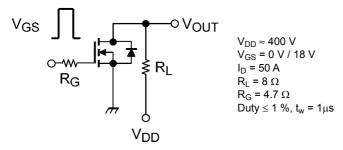
### 6.1. Static Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = +25/-10 V, V <sub>DS</sub> = 0 V		—	±0.1	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V		14	100	
			T <sub>a</sub> = 150 °C, V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V	—	72	_	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 4 mA, V <sub>GS</sub> = 0 V	650		_	V
Gate threshold voltage (N	Note 2)	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 11.7 mA	3.0	_	5.0	
Drain-source on-resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> = 18 V, I <sub>D</sub> = 50 A	—	15	21	mΩ
			T <sub>a</sub> = 150 °C, V <sub>GS</sub> = 18 V, I <sub>D</sub> = 50 A	_	16		

Note 2: Please be sure to apply  $I_{GSS}$  ( $V_{GS}$  = 25 V) before the  $V_{th}$  test.

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V,		4850	—	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 100 kHz	_	12	—	
Output capacitance	C <sub>oss</sub>		_	500	_	
Output charge	Q <sub>oss</sub>			337	—	nC
C <sub>oss</sub> stored energy	E <sub>oss</sub>		_	46	—	μJ
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz		1.0	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	79	—	ns
Switching time (turn-on time)	t <sub>on</sub>		_	117	—	
Switching time (fall time)	t <sub>f</sub>	]		59	_	
Switching time (turn-off time)	t <sub>off</sub>		_	116	_	





#### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)		$V_{DD} \approx 400$ V, $V_{GS}$ = 18 V, $I_D$ = 50 A	—	128	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	50	_	
Gate-drain charge	Q <sub>gd</sub>		_	19	_	

### 6.4. Source $\cdot$ Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 3)	I <sub>DR</sub>	T <sub>c</sub> = 25 °C, V <sub>GS</sub> = -5 V	_	_	100	A
			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = -5 V	—	_	73	
			T <sub>c</sub> = 25 °C, V <sub>GS</sub> = 18 V	_	_	100	
			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = 18 V	_	_	82	
Reverse drain current	(Note 3)	I <sub>DRP</sub>	T <sub>c</sub> = 25 °C, V <sub>GS</sub> = -5 V	_	_	360	
(pulsed)			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = -5 V	_	_	146	
			T <sub>c</sub> = 25 °C, V <sub>GS</sub> = 18 V	_	_	360	
			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = 18 V	_	_	270	
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = 45 A, V <sub>GS</sub> = -5 V	_	-1.35	-1.80	V
			T <sub>a</sub> = 150 °C, I <sub>DR</sub> = 45 A, V <sub>GS</sub> = -5 V	—	-1.64	_	
Reverse recovery time		t <sub>rr</sub>	I <sub>DR</sub> = 33 A, V <sub>GS</sub> = 0 V,	_	60	—	ns
Reverse recovery charge		Q <sub>rr</sub>	V <sub>DD</sub> = 400 V, -dI <sub>DR</sub> /dt = 1000 A/μs	_	510		nC
Peak reverse recovery current		I <sub>rr</sub>		—	17	_	A

Note 3: Ensure that the channel temperature does not exceed 175 °C.

### 7. Marking (Note)

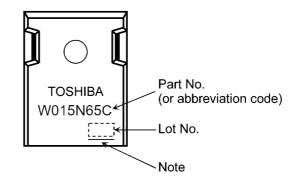
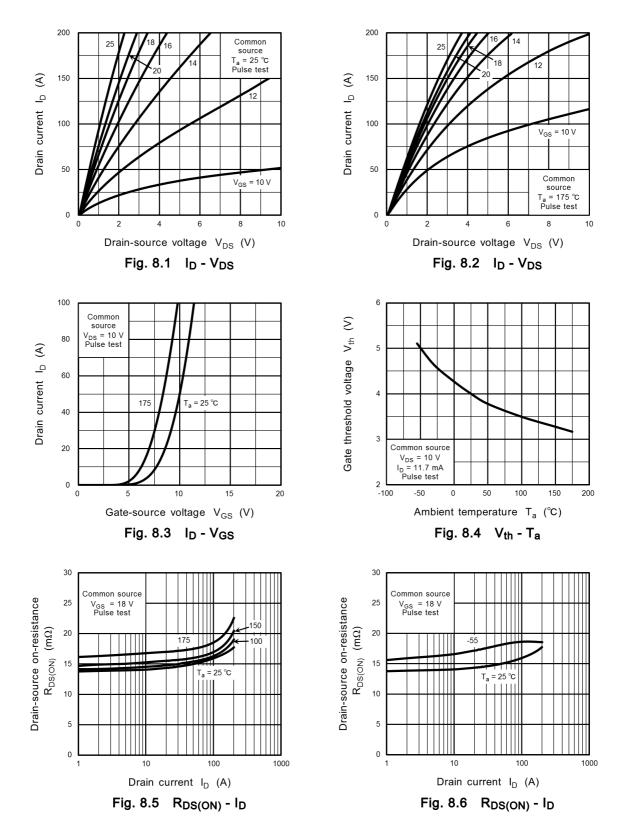
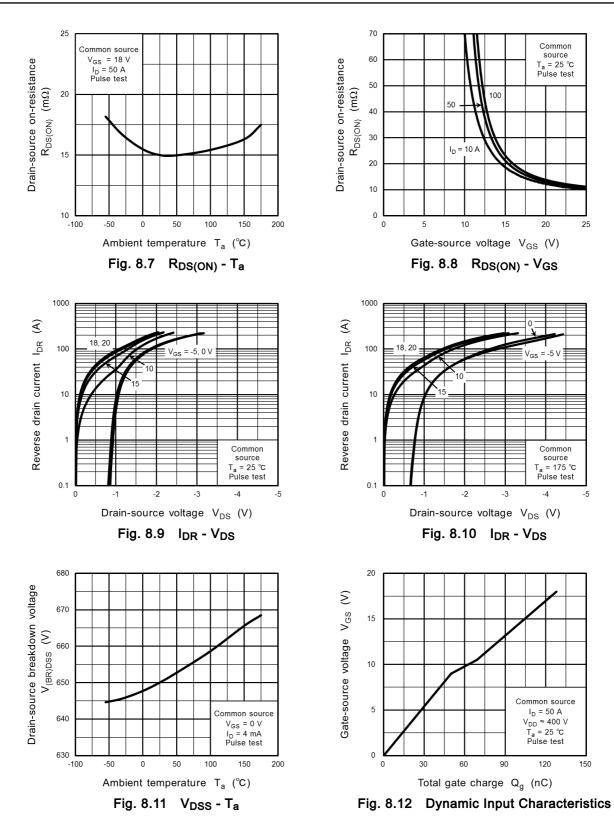


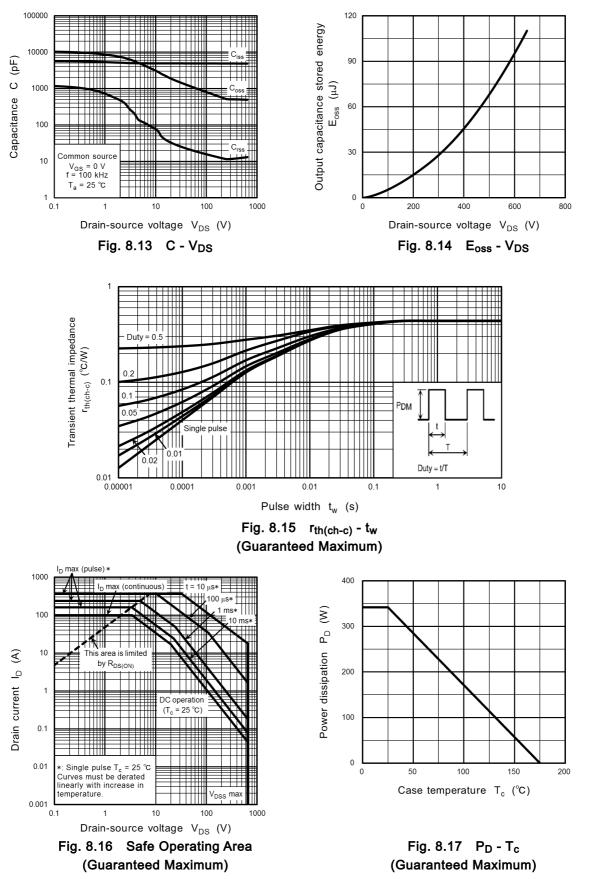
Fig. 7.1 Marking

 Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]
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#### 8. Characteristics Curves (Note)





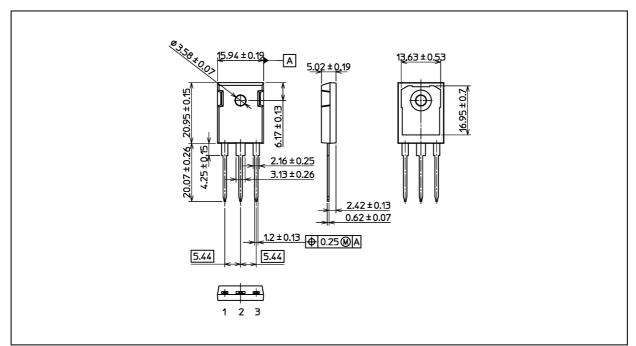


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### TW015N65C

### Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

	Package Name(s)
TOSHIBA: 2-16L1A	
Nickname: TO-247	

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